

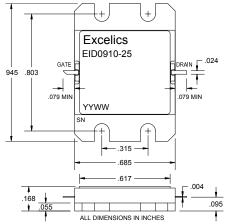


#### **UPDATED 06/14/2005**

## 9.50-10.50 GHz 25-Watt Internally Matched Power FET

### **FEATURES**

- 9.50-10.50GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +44 dBm Output Power at 1dB Compression
- 8.0 dB Power Gain at 1dB Compression
- 26% Power Added Efficiency
- -38 dBc IM3 at Po = 30.0 dBm SCL
- **Hermetic Metal Flange Package**
- 100% Tested for DC, RF, and R<sub>TH</sub>



# **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**



#### Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS <sup>1</sup>	MIN	TYP	MAX	UNITS
P <sub>1dB</sub>	Output Power at 1dB Compression $f = 9.50-10.50GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 4000\text{mA}$	43	44		dBm
G <sub>1dB</sub>	Gain at 1dB Compression $f = 9.50-10.50GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 4000\text{mA}$	7.0	8.0		dB
ΔG	Gain Flatness $f = 9.50-10.50GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 4000\text{mA}$			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS}$ = 10 V, $I_{DSQ} \approx 4000$ mA f = 9.50-10.50GHz		26		%
$Id_{1dB}$	Drain Current at 1dB Compression f = 9.50-10.50GHz		8000	9000	mA
IM3	Output 3rd Order Intermodulation Distortion $\Delta f$ = 10 MHz 2-Tone Test; Pout = 30.0 dBm S.C.L <sup>2</sup> $V_{DS}$ = 10 V, $I_{DSQ}$ ≈ 65% IDSS $f$ = 10.50GHz	-33	-38		dBc
I <sub>DSS</sub>	Saturated Drain Current V <sub>DS</sub> = 3 V, V <sub>GS</sub> = 0 V		14000	18000	mA
$V_P$	Pinch-off Voltage $V_{DS} = 3 \text{ V}, I_{DS} = 140 \text{ mA}$		-1.2	-2.5	V
R <sub>TH</sub>	Thermal Resistance <sup>2</sup>		1.4	1.6	°C/W

Note: 1) Tested with 25 Ohm gate resistor.

2) Overall Rth depends on case mounting.

### **ABSOLUTE MAXIMUM RATING**<sup>1,2</sup>

SYMBOL	CHARACTERISTIC	VALUE
$V_{DS}$	Drain to Source Voltage	10 V
$V_{GS}$	Gate to Source Voltage	-3.0 V
I <sub>DS</sub>	Drain Current	IDSS
$I_{GSF}$	Forward Gate Current	500 mA
P <sub>IN</sub>	Input Power	@ 3dB compression
$P_{T}$	Total Power Dissipation	94 W
$T_CH$	Channel Temperature	175°C
T <sub>STG</sub>	Storage Temperature	-65/+175°C

Notes: 1. Exceeding any of the above ratings may result in permanent damage.
2. Exceeding any of the above ratings may reduce MTTF below design goals.